

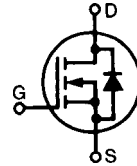
# HiPerFET™ Power MOSFETs

N-Channel Enhancement Mode  
High dv/dt, Low  $t_{rr}$ , HDMOS™ Family

**IXFH14N80**  
**IXFH15N80**

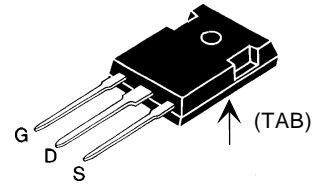
$V_{DSS}$	$I_{D25}$	$R_{DS(on)}$
<b>800 V</b>	<b>14 A</b>	<b>0.70 <math>\Omega</math></b>
<b>800 V</b>	<b>15 A</b>	<b>0.60 <math>\Omega</math></b>

**$t_{rr} \leq 250$  ns**



Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	800	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1$ M $\Omega$	800	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	14N80	14 A
		15N80	15 A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	14N80	56 A
		15N80	60 A
$I_{AR}$	$T_C = 25^\circ\text{C}$	14N80	14 A
		15N80	15 A
$E_{AR}$	$T_C = 25^\circ\text{C}$	30	mJ
dv/dt	$I_S \leq I_{DM}$ , $di/dt \leq 100$ A/ $\mu\text{s}$ , $V_{DD} \leq V_{DSS}$	5	V/ns
	$T_J \leq 150^\circ\text{C}$ , $R_G = 2$ $\Omega$		
$P_D$	$T_C = 25^\circ\text{C}$	300	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
Weight		6	g

TO-247 AD



G = Gate      D = Drain  
S = Source      TAB = Drain

## Features

- International standard packages
- Low  $R_{DS(on)}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance - easy to drive and to protect
- Fast intrinsic Rectifier

## Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls
- Low voltage relays

## Advantages

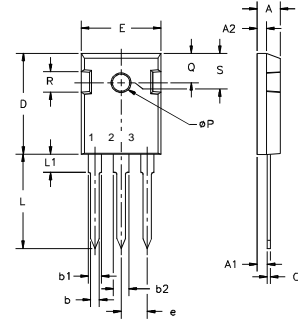
- Easy to mount with 1 screw (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{DSS}$	$V_{GS} = 0$ V, $I_D = 3$ mA	800		V
	$V_{DSS}$ temperature coefficient		0.096	%/K
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4$ mA	2.5		4.5 V
	$V_{GS(th)}$ temperature coefficient		-0.214	%/K
$I_{GSS}$	$V_{GS} = \pm 20$ V <sub>DC</sub> , $V_{DS} = 0$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $T_J = 25^\circ\text{C}$			25 $\mu\text{A}$
	$V_{GS} = 0$ V, $T_J = 125^\circ\text{C}$			1 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 0.5 I_{D25}$	14N80		0.70 $\Omega$
	Pulse test, $t \leq 300$ $\mu\text{s}$ , duty cycle $d \leq 2$ %	15N80		0.60 $\Omega$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = 0.5 I_{D25}$ , pulse test	8	14	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	3965		4870 pF
$C_{oss}$		315		395 pF
$C_{rss}$		73		120 pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2\ \Omega$ (External)		20	50 ns
$t_r$			33	50 ns
$t_{d(off)}$			63	100 ns
$t_f$			32	50 ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		150	200 nC
$Q_{gs}$			23	45 nC
$Q_{gd}$			64	68 nC
$R_{thJC}$				0.42 KW
$R_{thCK}$		0.25		KW

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$	14N80 15N80		14 A 15 A
$I_{SM}$	Repetitive;	14N80 15N80		56 A 60 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = I_S$ $-di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$	$T_J = 25^\circ\text{C}$		250 ns
$Q_{RM}$		$T_J = 125^\circ\text{C}$		400 ns
$I_{RM}$			1	$\mu\text{C}$
			8.5	A

### TO-247 AD Outline



Terminals: 1 - Gate    2 - Drain  
3 - Source    Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

Figure 1. Output Characteristics at 25°C

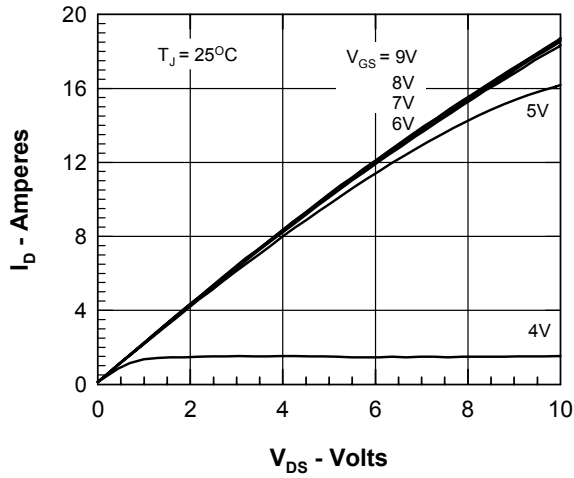


Figure 2. Output Characteristics at 125°C

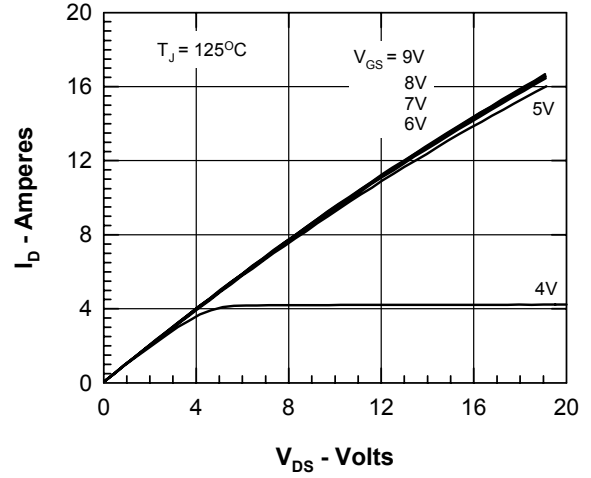


Figure 3.  $R_{DS(on)}$  normalized to 0.5  $I_{D25}$  value vs.  $I_D$

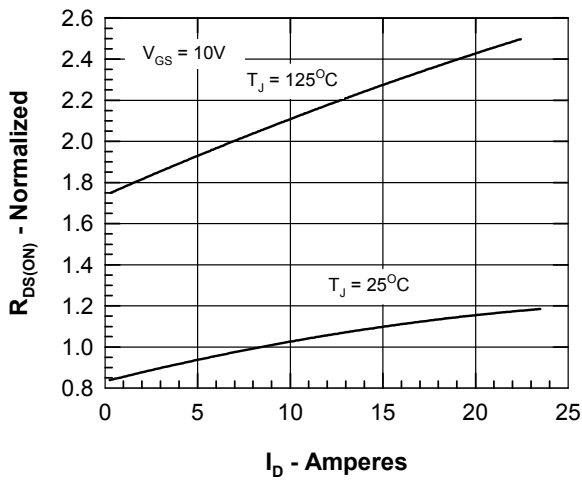


Figure 4.  $R_{DS(on)}$  normalized to 0.5  $I_{D25}$  value vs.  $T_J$

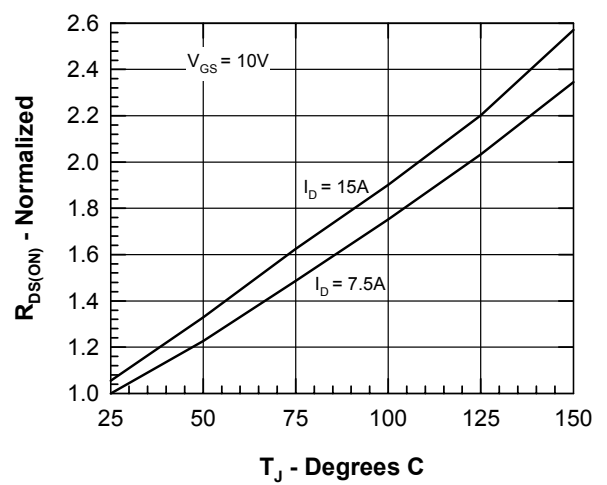


Figure 5. Drain Current vs. Case Temperature

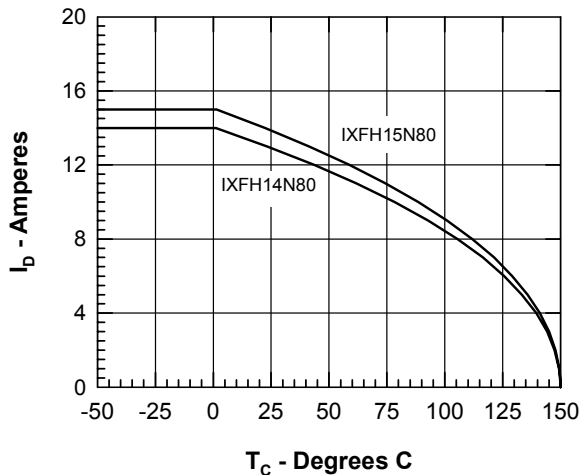


Figure 6. Admittance Curves

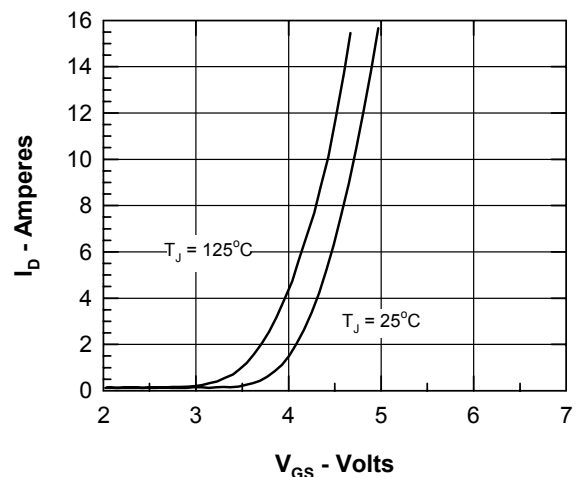


Figure 7. Gate Charge

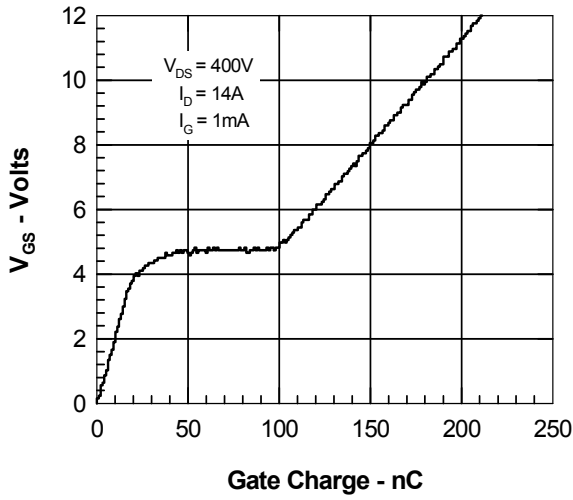


Figure 8. Capacitance Curves

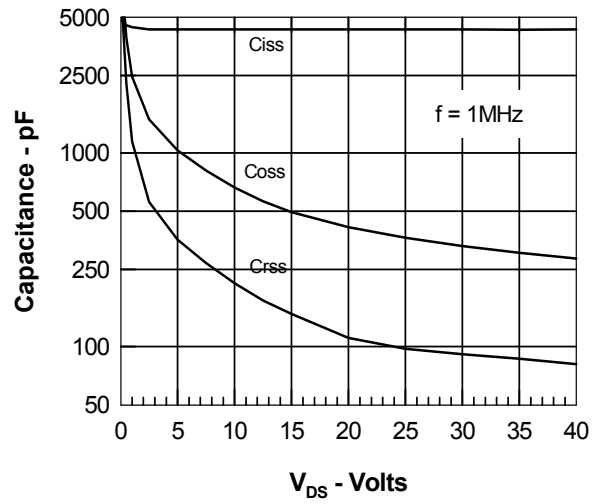


Figure 9. Source Current vs. Source to Drain Voltage

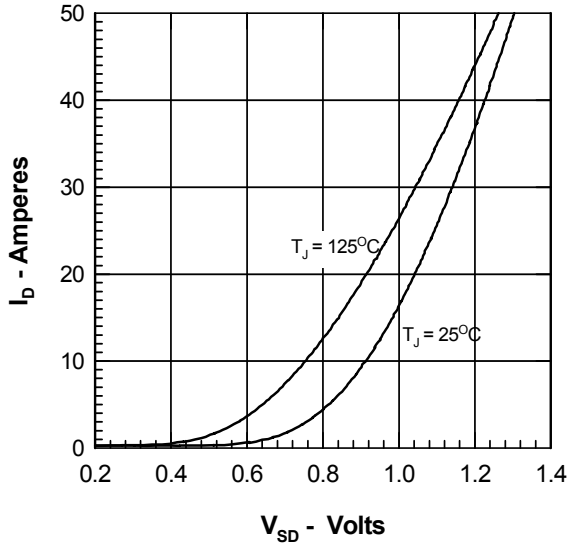
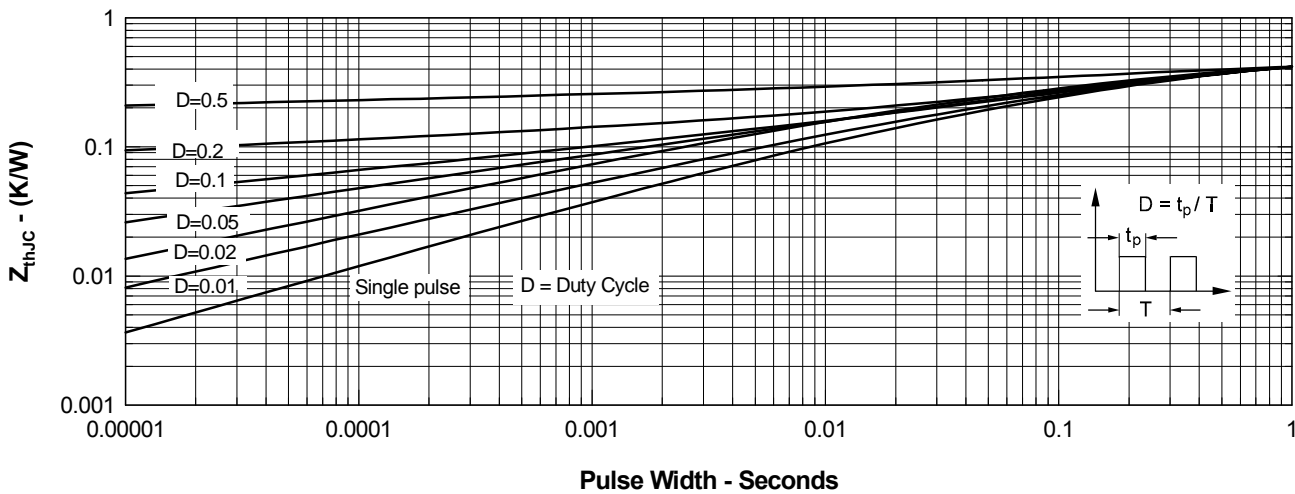


Figure 11. Transient Thermal Resistance



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	